

Three Phase AC Controller Modules

PSUH 40

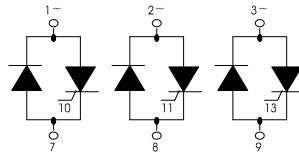
$$\begin{matrix} I_{\text{RMS}} \\ V_{\text{RRM}} \end{matrix}$$

= 3 x 40A
= 400-1600 V

Preliminary Data Sheet

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type
500	400	PSUH 40/04
900	800	PSUH 40/08
1300	1200	PSUH 40/12
1500	1400	PSUH 40/14
*1700	*1600	PSUH 40/16

* Delivery on request



Symbol	Test Conditions	Maximum Ratings
I_{RMS}	T _C = 85 °C, 50-400 Hz (per phase)	40 A
I_{TRMS}	T _{VJ} = T _{VJM}	29 A
I_{TAVM}	T _C = 85 °C 180° sine	18 A
I_{TSM}	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	400 A
	V _R = 0 t = 8.3 ms (60 Hz), sine	450 A
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	360 A
	V _R = 0 t = 8.3 ms (60 Hz), sine	390 A
∫ i² dt	T _{VJ} = 45°C t = 10 ms (50 Hz), sine	800 A ² s
	V _R = 0 t = 8.3 ms (60 Hz), sine	850 A ² s
	T _{VJ} = T _{VJM} t = 10 ms (50 Hz), sine	650 A ² s
	V _R = 0 t = 8.3 ms (60 Hz), sine	640 A ² s
(di/dt)_{cr}	T _{VJ} = T _{JVM} repetitive, I _T = 150 A	100 A/μs
	f = 50Hz, t _p = 200μs	
	V _D = 2/3 V _{DRM}	
	I _G = 0.3 A non repetitive, I _T = I _{TAVM}	500 A/μs
	di _G /dt = 0.3 A/μs	
(dv/dt)_{cr}	T _{VJ} = T _{VJM} V _{DR} = 2/3 V _{DRM}	1000 V/μs
	R _{GK} = ∞, method 1 (linear voltage rise)	
P_{GM}	T _{VJ} = T _{VJM} t _p = 30μs	10 W
	I _T = I _{TAVM} t _p = 300μs	5 W
P_{GAVM}		0.5 W
V_{RGM}		10 V
T_{VJ}		-40 ... + 125 °C
T_{VJM}		125 °C
T_{stg}		-40 ... + 125 °C
V_{ISOL}	50/60 HZ, RMS t = 1 min	2500 V ~
	I _{ISOL} ≤ 1 mA t = 1 s	3000 V ~
M_d	Mounting torque (M5)	5 Nm
	Terminal connection torque (M3)	1.5 Nm
	(M5)	5 Nm
Weight	typ.	220 g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Package with metal base plate
- UL registered E 148688

Applications

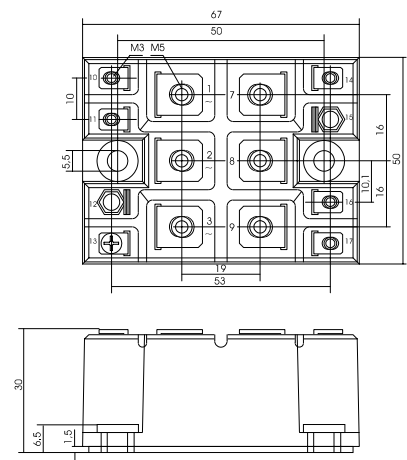
- Switching and control of three phase AC circuits
- Light and temperature control
- Softstart AC motor controller
- Solid state switches

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

Package, stil and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions	Characteristic Value
I_D, I_R	$T_{VJ} = T_{VJM}, V_R = V_{RRM}, V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 80A, T_{VJ} = 25^\circ C$	≤ 1.65 V
V_{TO}	For power-loss calculations only ($T_{VJ} = T_{VJM}$)	0.85 V
r_T		15 m Ω
V_{GT}	$V_D = 6V, T_{VJ} = 25^\circ C$	≤ 1.0 V
	$T_{VJ} = -40^\circ C$	≤ 1.6 V
I_{GT}	$V_D = 6V, T_{VJ} = 25^\circ C$	≤ 100 mA
	$T_{VJ} = -40^\circ C$	≤ 150 mA
V_{GD}	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = T_{VJM}, V_D = 2/3 V_{DRM}$	≤ 5 mA
I_L	$T_{VJ} = 25^\circ C, t_p = 10\mu s$	≤ 200 mA
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$	
I_H	$T_{VJ} = 25^\circ C, V_D = 6V, R_{GK} = \infty$	≤ 150 mA
t_{gd}	$T_{VJ} = 25^\circ C, V_D = 1/2 V_{DRM}$	≤ 2 μs
	$I_G = 0.3A, di_G/dt = 0.3A/\mu s$	
t_q	$T_{VJ} = T_{VJM}, I_T = 20A, t_p = 200\mu s, V_R = 100V$ $-di/dt = 10A/\mu s, dv/dt = 15V/\mu s, V_D = 2/3 V_{DRM}$	150 μs
R_{thJC}	per thyristor; sine 180°el	1.43 K/W
	per module	0.238 K/W
R_{thJK}	per thyristor; sine 180° el	1.53 K/W
	per module	0.255 K/W
d_s	Creeping distance on surface	8.0 mm
d_A	Creeping distance in air	4.5 mm
a	Max. allowable acceleration	50 m/s ²